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Michael Grätzel
Hiroshi Amano
Chin Hsin Chen
Changqing Chen
Peng Wang
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## Contents

<table>
<thead>
<tr>
<th>Session</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>7518 02</td>
<td><strong>AlGaN-based material characterizations and recent development of related solar-blind ultraviolet detectors (Invited Paper)</strong> [7518-49]</td>
<td>X. Li, J. Xu, Y. Zhang, Y. Yuan, K. Chu, C. Li, X. Bao, L. Wang, Shanghai Institute of Technical Physics (China)</td>
</tr>
<tr>
<td>7518 03</td>
<td><strong>Bright and color-saturated quantum dot light-emitting diodes: new star for next generation displays and solid state lighting</strong> [7518-26]</td>
<td>Z. Tan, North China Electric Power Univ. (China); J. Xu, T. Zhu, The Pennsylvania State Univ. (United States); A. Y. Wang, Ocean Nano Tech LLC (United States); Q. Sun, Y. Li, Institute of Chemistry (China); Y. Yang, North China Electric Power Univ. (China)</td>
</tr>
<tr>
<td>7518 04</td>
<td><strong>Cadmium sulfide quantum dots grown by chemical bath deposition for sensitized solar cell applications</strong> [7518-11]</td>
<td>D. W. Zhang, S. Chen, East China Normal Univ. (China); X. D. Li, East China Normal Univ. (China) and Singapore Polytechnic (Singapore); Z. A. Wang, J. H. Shi, Z. Sun, East China Normal Univ. (China); X. J. Yin, Singapore Polytechnic (Singapore); S. M. Huang, East China Normal Univ. (China)</td>
</tr>
<tr>
<td>7518 05</td>
<td><strong>Centrotherm’s high end CIGS thin film turnkey solution (Invited Paper)</strong> [7518-62]</td>
<td>D. Schmid, I. Koetschau, A. Kampmann, T. Hahn, J. Hinze, W. Zhang, centrotherm Photovoltaics AG (Germany)</td>
</tr>
<tr>
<td>7518 06</td>
<td><strong>Density functional study of neutral and charged titanium dioxide clusters</strong> [7518-52]</td>
<td>D. Li, Z. Xiong, Q. Wan, Jiangxi Science and Technology Normal Univ. (China); Y. Lv, Nanchang Univ. (China); J. Peng, Jiangxi Science and Technology Normal Univ. (China)</td>
</tr>
<tr>
<td>7518 07</td>
<td><strong>Design and analysis of solar energy photovoltaic system</strong> [7518-16]</td>
<td>T. Li, C. Jiang, X. Zhang, L. Hou, Shandong Univ. of Technology (China)</td>
</tr>
<tr>
<td>7518 08</td>
<td><strong>Effects of substrate temperature on properties of the aluminum-doped zinc oxide thin films deposited by RF magnetron sputtering</strong> [7518-44]</td>
<td>Y. Yang, X. Zeng, Huazhong Univ. of Science and Technology (China)</td>
</tr>
<tr>
<td>7518 09</td>
<td><strong>Effects of the thickness of low-temperature AlN interlayers on GaN layers grown on Si(111) substrates by MOCVD</strong> [7518-64]</td>
<td>R. F. Xiang, J. N. Dai, L. Zhang, Y. Gao, Z. H. Wu, C. Q. Chen, Huazhong Univ. of Science and Technology (China); Q. Feng, Xidian Univ. (China); Y. Hao, Huazhong Univ. of Science and Technology (China) and Xidian Univ. (China)</td>
</tr>
</tbody>
</table>
7518 0A Efficiency enhancement of GaN-based LED using nanotechnology (Invited Paper) [7518-50]
C. H. Chiu, M. A. Tsai, P. Yu, H. C. Kuo, National Chiao Tung Univ. (Taiwan, China)

7518 0B Electrochemical study on the TiO2 porous electrodes for metal-free dye-sensitized solar cells [7518-12]
D. W. Zhang, S. Chen, East China Normal Univ. (China); X. D. Li, East China Normal Univ. (China) and Singapore Polytechnic (Singapore); Z. A. Wang, J. H. Shi, Z. Sun, East China Normal Univ. (China); X. J. Yin, Singapore Polytechnic (Singapore); S. M. Huang, East China Normal Univ. (China)

7518 0C Field-emission SEM characterization of novel ZnO thin films grown by magnetron sputtering on the different substrates [7518-37]
T. Peng, X. Xiao, C. Jiang, Wuhan Univ. (China)

7518 0D First-principles calculations of crystal structure of AgxZn1-xO alloys [7518-33]
Q. Wan, Z. Xiong, D. Li, G. Liu, Jiangxi Science and Technology Normal Univ. (China)

7518 0E First-principles study on distribution of Ag in ZnO [7518-30]
Q. Wan, Z. Xiong, D. Li, G. Liu, J. Peng, Jiangxi Science and Technology Normal Univ. (China)

7518 0F GaP single crystal layers grown on GaN by MOCVD [7518-13]
S. Li, J. Cao, G. Fan, Y. Zhang, S. Zheng, H. Sun, J. Su, South China Normal Univ. (China)

7518 0G High-resolution x-ray diffraction studies of highly curved GaN layers prepared by hydride vapor phase epitaxy [7518-27]
J. Q. Liu, Suzhou Institute of Nano-Tech and Nano-Bionics (China), Institute of Semiconductors (China), and Graduate Univ. of Chinese Academy of Sciences (China); Y. X. Qiu, J. F. Wang, Suzhou Institute of Nano-Tech and Nano-Bionics (China); X. Guo, Institute of Semiconductors (China); K. Huang, K. Xu, H. Yang, Suzhou Institute of Nano-Tech and Nano-Bionics (China)

7518 0H ICP etching of high Al mole fraction AlGaN [7518-18]
Z. Meng, L. Yu, X. Li, Q. Liu, Southwest Institute of Technical Physics (China); H. Duan, C. Yu, C. Chen, Huazhong Univ. of Science and Technology (China)

7518 0I Improved performance of organic light emitting devices using triazole/ Cs2CO3/Al cathode [7518-46]
J. Lian, Shenzhen Univ. (China); H. Xu, South China Agricultural Univ. (China); F. Niu, Y. Liu, P. Zeng, Shenzhen Univ. (China)

7518 0J Influence of alumina coating on transport and recombination in DSSCs with 1-methylbenzimidazole as electrolyte additives [7518-38]
X. Xu, Guangzhou Institute of Energy Conversion (China); E. M. Barea, F. Fabregat-Santiago, J. Bisquert, Univ. Jaume I (Spain); G. Xu, Guangzhou Institute of Energy Conversion (China)

7518 0K Influence of different parameter profiles on the formation of aluminum back surface field (Al-BSF) using for HIT solar cell [7518-10]
X. Zeng, Y. Zeng, Q. A. H. Al-Naser, Huazhong Univ. of Science and Technology (China); C. Zhou, Institute of Electrical Engineering (China); X. Zhang, Q. Chen, Y. Yang, L. Liu, Huazhong Univ. of Science and Technology (China)
Influence of the base layer thickness and the graded buffer layer thickness on the conversion efficiency of a metamorphic triple-junction solar cell [7518-58]
M. Song, H. Wang, Y. Xiong, Y. Sun, C. Yu, Z. Wu, C. Chen, Huazhong Univ. of Science and Technology (China)

Investigation of photoelectrochemical etching of textured silicon in solar cells [7518-09]
J. You, J. Shi, B. Peng, L. Wang, East China Normal Univ. (China); P. K. Chu, City Univ. of Hong Kong (Hong Kong, China)

Junction temperature measurement on light-emitting diodes and its application (Invited Paper) [7518-59]
S. M. He, B. Zhang, N. Li, S. S. Liu, T. Zhang, W. Lu, Shanghai Institute of Optics and Fine Mechanics (China)

Minority carrier mobility measurement in HgCdTe with light-modulated Hall effect [7518-29]
F. Yin, B. Zhang, Shanghai Institute of Technical Physics (China)

Novel materials for high-efficiency solar cells (Invited Paper) [7518-60]
N. Kojima, M. Natori, H. Suzuki, M. Inagaki, Y. Ohshita, M. Yamaguchi, Toyota Technological Institute (Japan)

Numerical simulation study of a distributed fiber-optic lighting system [7518-23]
S. Li, H. Gong, China Jiliang Univ. (China); Y. Hong, Changqing Oil Field Co., Ltd. (China); J. Chen, China Jiliang Univ. (China)

Optical properties of BiFeO3 films grown by Sol-gel method [7518-05]
G. Sheng, L. Zeng, Z. Liu, Z. Zhang, P. Yang, East China Normal Univ. (China)

Preparation and photoelectric properties of Fe-doped mesoporous TiO2 thick films used in DSSC [7518-40]
Y. Xie, Y. Shen, F. Gu, H. Lu, M. Wu, L. Wang, Shanghai Univ. (China)

Preparation and photoelectric properties of mesoporous ZnO/TiO2 composite films for DSSC [7518-36]
M. Wu, Y. Shen, F. Gu, Y. Zhang, Y. Xie, J. Zhang, Shanghai Univ. (China)

Preparation of BST ferroelectric thin films by pulsed laser deposition for infrared sensor [7518-06]
L. Zeng, G. Sheng, Z. Zhang, P. Yang, East China Normal Univ. (China)

Removal and passivation of surface defects in perforated GaN-based light-emitting diodes (Invited Paper) [7518-20]
Y. Yang, X. A. Cao, West Virginia Univ. (United States)

Research on light capture of solar cell and its application [7518-15]
T. Li, L. Hou, C. Jiang, L. Ma, Shandong Univ. of Technology (China)

Research on transparent conductive AZO film fabricated by PECVD method [7518-02]
Z. Chen, M. Liu, Y. Liu, P. Hu, L. Tang, X. Hu, Huazhong Univ. of Science and Technology (China)
Structural and optical properties of Bi$_2$VO$_{5.5}$ thin films deposited on silicon substrates [7518-31]
Z. Zhang, Z. Liu, M. Guo, P. Yang, East China Normal Univ. (China)

Z. Xiong, L. Chen, D. Li, Q. Wan, Jiangxi Univ. of Science and Technology (China)

Study on performance of p-Si thin film fabricated by aluminum induced lateral crystallization at low temperature [7518-19]
Q. Chen, X. Zeng, Y. Zeng, L. Liu, Y. Yang, Huazhong Univ. of Science and Technology (China)

The design of back surface field layer for a single GaAs solar cell [7518-54]
Y. Xiong, Huazhong Univ. of Science and Technology (China); K. Tang, Hebei Semiconductor Research Institute (China); M. Song, C. Feng, Y. Sun, C. Yu, Z. Wu, H. Xiong, C. Chen, Huazhong Univ. of Science and Technology (China)

The electrical and optical properties of doped BTO thin films [7518-22]
Z. Liu, Z. Zhang, G. Sheng, P. Yang, J. Chu, East China Normal Univ. (China)

The evaluation and measurement of AlGaN epitaxial layer with high Al mole fraction [7518-07]
Z. Meng, L. Yu, X. Li, Q. Liu, South-West Institute of Technical Physics (China); H. Duan, C. Yu, C. Chen, Huazhong Univ. of Science and Technology (China)

The improvement of ohmic contact of Ti/Al/Ni/Au to AlGaN/GaN HEMT by multi-step annealing method [7518-55]
Q. Feng, L. Li, Y. Hao, Z. Bi, Xidian Univ. (China)

The optical properties of rare-earth multi-ferroelectric thin-film LuFeO$_3$ and LuFe$_{1-x}$Mn$_x$O$_3$ fabricated with Sol-gel method [7518-47]
T. Xu, L. Zhu, P. Yang, J. Chu, Ministry of Education (China)

Theoretical investigation of three dimensional p-n junctions for improvement of silicon solar cell efficiency [7518-04]
J. Shi, J. You, L. Wang, East China Normal Univ. (China); P. K. Chu, City Univ. of Hong Kong (Hong Kong, China)

Visible luminescence from Dy$^{3+}$ doped tellurite glasses [7518-41]
F. Zhang, Z. Xiao, L. Yan, F. Zhu, A. Huang, Beihang Univ. (China)

Wet chemical etching of Al$_{0.65}$Ga$_{0.35}$N in aqueous KOH solutions [7518-48]
J. Xu, J. Chen, Z. Su, Y. Zhang, X. Li, Shanghai Institute of Technical Physics (China)

Synthesis and characterization of two kind of deep blue emission organic small molecular materials [7518-56]
H. Zhao, F. Zhang, L. Cai, Beijing Aglaia Technology Development Co., Ltd. (China)

AIN based diluted magnetic semiconductors from first-principles study [7518-21]
K. Zeng, Z.-Y. Guo, H.-X. Zhao, X.-Q. Gao, South China Normal Univ. (China)
Electronic structure and the optical properties of GaN (0001) surface from first-principles study [7518-17]
H. Zhao, Z. Guo, K. Zeng, X. Gao, South China Normal Univ. (China)

Numerical modeling of thermionic electrons in abrupt isotype heterojunction for the light emitting transistor [7518-14]
H. Zhao, Z. Guo, K. Zeng, X. Gao, South China Normal Univ. (China)

Simulation and analysis of GaN-based light-emitting diodes with diamond shaped [7518-39]
B. Cao, P. Wang, Z. Gan, S. Liu, Huazhong Univ. of Science and Technology (United States)

Theoretical study on optimization of high efficiency GaInP/GaInAs/Ge tandem solar cells [7518-01]
G. J. Lin, S. R. Huang, Xiamen San'an Optoelectronics Co., Ltd (China) and Xiamen Univ. (China); J. C. Wu, Xiamen San'an Optoelectronics Co., Ltd (China); M. C. Huang, Xiamen Univ. (China)

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